

# Remote-control spin filtering through a $T$ -type structure

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We propose a spin filter scheme using a  $T$ -stub waveguide. By applying a moderate magnetic field at the tip of the sidearm, this device can produce both large electric and spin current. The direction, polarization of the output spin current can be further adjusted electronically by a remote gate which tunes the length of the sidearm. The device is robust against the disorder.

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Spintronic devices have many advantages over the traditional electronic devices such as higher operation speed, lower power consumption.<sup>1,2,3</sup> Tremendous efforts have been devoted in the past few years to overcome the fundamental obstacles in the realization of spintronic devices, such as spin generation, control and detection. Direct injection of spin current from ferromagnetic metal or semiconductor was first proposed to realize the spin injection.<sup>4,5</sup> Despite the great efforts, the highest spin injection rate reported is about 90%<sup>4</sup> for p-typed and 57%<sup>6</sup> for n-typed semiconductor. A great number of schemes of spin filter have been proposed to produce highly polarized spin current using various of structures such as electronic waveguide,<sup>7,8</sup> double-bend structure,<sup>9</sup> Aharonov-Bohm (AB) ring,<sup>10</sup> resonant tunneling diode,<sup>11</sup> quantum dot,<sup>12,13,14</sup> ferromagnetic electrode.<sup>15</sup> More recently, the spin filter for the hole system was brought to public.<sup>16</sup> Dynamical spin generation in semiconductor using oscillation field is also proposed to avoid the difficulty of spin injection through interface.<sup>17,18</sup>

In this paper, we propose a spin filter scheme which can produce high spin polarization (SP) and also provides remote control of spin current magnetically as well as electronically. Our scheme is a localized magnetic field modulated 2-dimensional (2D)  $T$ -stub waveguide as shown in Fig. 1. The waveguide is composed of a longitudinal conductor with length  $L$ , width  $N_y$  and a sidearm of width  $N_x$  attached to the center of the conductor. The effective conducting length of sidearm  $L_s$  can be controlled by the remote gate voltage  $V_g$  which changes  $L_d$ , the length of depletion area (area B in Fig. 1. The far edge of sidearm (gray areas A and B in the Fig. 1) is modulated by an applied magnetic field which gives Zeeman splitting of  $2V_0$ .  $T$ -stub geometry has long been proposed as quantum modulated transistor (QMT).<sup>19,20</sup> The conductance of this kind of devices is determined by the quantum interference effect between different Feynman paths and oscillates with the Fermi energy. When a modulate magnetic field is applied, the electrons of different spins will have different phase shifts transpassing through the modulated area and therefore have different conductances. In this way, the non-spin-polarized electron current pass through this device will produce SP. The spin current can

also be controlled electronically by the remote gate by adjusting the effective sidearm length  $L_s$ . It is worth noting that our spin filter is different from other implementations in the fact that our device can be *remotely* controlled by both magnetical and electronic methods while the other ones can only be controlled locally. Moreover our device has more energy windows to generate high polarized spin current than the device made by a single quantum dot.<sup>14</sup>

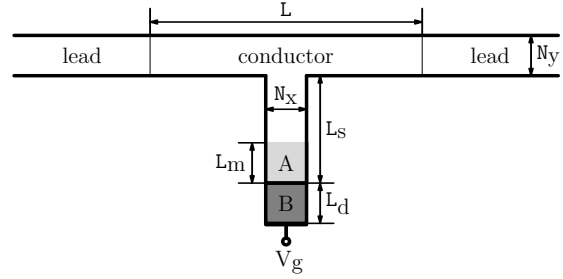


FIG. 1: Schematic of remote-control spin filter in  $T$ -stub waveguide. The modulating field is applied only at the tip of the sidearm (area A and B).

We describe the  $T$ -stub geometry by the tight-binding Hamiltonian with nearest-neighbor approximation:

$$H = \sum_{l,m,\sigma} \varepsilon_{l,m,\sigma} c_{l,m,\sigma}^\dagger c_{l,m,\sigma} + t_0 \sum_{l,m,\sigma} (c_{l+1,m,\sigma}^\dagger c_{l,m,\sigma} + c_{l,m+1,\sigma}^\dagger c_{l,m,\sigma} + h.c.) \quad (1)$$

in which  $l$  and  $m$  denote the “lattice” site index along the  $x$ - and  $y$ -axis respectively. The on-site energy  $\varepsilon_{l,m,\sigma} = \varepsilon_0 + \sigma V_0$  when  $(l,m)$  locates in the modulated regime (the gray area in the Fig. 1) and  $\varepsilon_0$  otherwise.  $\varepsilon_0 = -4t_0$  and  $t_0 = -\hbar/(2m^*a^2)$  is the hopping energy with  $m^*$  and  $a$  standing for the effective mass and the “lattice” constant respectively.  $\sigma V_0$  is the Zeeman energy of spin  $\sigma$  in the modulate magnetic field and  $\sigma = \pm 1$  for spin-up and -down electrons respectively.

The two-terminal spin-dependent conductance is obtained by using Landauer-Büttiker<sup>21</sup> formula  $G^{\sigma\sigma'}(E) =$



$(e^2/h)\text{Tr}[\Gamma_1^\sigma G_{1L}^{\sigma\sigma'+}(E)\Gamma_N^{\sigma'} G_{L1}^{\sigma'\sigma-}(E)]$  with  $\Gamma_{1/N}^\sigma$  representing the self-energy function for the isolated left/right ideal leads.<sup>22</sup>  $G_{1L}^{\sigma\sigma'+}(E)$  and  $G_{L1}^{\sigma'\sigma-}(E)$  are the full retarded and advanced Green functions for the conductor which have taken account the effect of the leads.  $\text{Tr}$  stands for the trace over the  $y$ -axis. The spin dependent current is given by  $I_\sigma = \int_E^{E+\Delta} G^{\sigma\sigma}(\varepsilon)d\varepsilon$  for energy window  $[E, E + \Delta]$ .

We first study the analytically solvable transport problem in quasi-one-dimensional ( $N_x = N_y = 1$ ) T-stub geometry system. By solving the time independent Schrödinger equation,<sup>23</sup> the transmission coefficient in this system can be written as

$$t_\sigma = 2iG_{0,0}^{\sigma\sigma}(E)t_0^3 \sin(ka) / \{[\varepsilon_1 - E + t_0 e^{ika} + G_{0,0}^{\sigma\sigma}(E)t_0^2] \times [\varepsilon_{-1} - E + t_0 e^{ika} + G_{0,0}^{\sigma\sigma}(E)t_0^2] - [G_{0,0}^{\sigma\sigma}(E)t_0^2]^2\}, \quad (2)$$

in which  $G_{l,m}^{\sigma\sigma'}(E) = (E - \hat{H})_{l\sigma,m\sigma'}^{-1}$  and  $\hat{H}$  are the Green function and the Hamiltonian of sidearm respectively.  $E = 2|t_0|(1 - \cos(ka))$  is the energy of electron with wave-vector  $k$ . The corresponding conductance is  $G^\sigma = (e^2/h)|t_\sigma|^2$ . Without the modulation, the transmission coefficient drops to zero at the anti-resonance points  $2|t_0|[1 - \cos(n\pi/(L_s + 1))](n = 1, 2, \dots)$  and reaches its maximum quickly at resonance points  $2|t_0|[1 - \cos(n\pi/L_s)](n = 1, 2, \dots)$ . When the modulate field turns on, the (anti-)resonance points of spin-up and -down shift apart. In Fig. 2(a) we plot spin resolved conductance as a function of the electron energy for a typical quasi-one-dimensional T-stub device with sidearm length  $L_s = 63a$ , magnetic field  $V_0 = 0.001|t_0|$  and modulation length  $L_m = 10a$ . Since a pair of anti-resonance and resonance points are very close to each other when the sidearm is relatively long, it is possible to choose the system parameters so that the resonance point of spin-up (-down) electron matches the anti-resonance point of spin-down (-up) electron under moderate magnetic field. In this way, we can obtain both large electric current and large spin current.

We now study the transport in T-stub waveguide with finite conductor and sidearm widths. We carry out a numerical calculation for a waveguide whose geometry parameters are  $L = 60a$ ,  $N_x = 10a$ ,  $N_y = 10a$ . The leads are assumed to have perfect Ohmic contacts with the conductor. A hard wall potential is applied at the edge of the waveguide. This makes the lowest energy of  $n$ -th subband (mode) in leads be  $\varepsilon_n = 2|t_0|\{1 - \cos[n\pi/(N_y + 1)]\}$ . The Fermi energy in our calculation is between  $0.083|t_0|$  and  $0.124|t_0|$  so that only the lowest mode contributes to the conductance. The Zeeman splitting energy is  $V_0 = 0.001|t_0|$  corresponding to a few Teslas for the typical III-V semiconductors with lattice constant  $a = 20\text{\AA}$ . In Fig. 2(b) we present the electron conductance as a function of the injection electron energy for a device with  $L_s = 60a$  and  $L_m = 15a$ . Noted that the energy is count from bottom of the first mode. It is seen from the figure that many properties of quasi-one-dimensional T-stub waveguide survive in the finite width one: The

conductance oscillates with the injection energy. It approaches to zero at the anti-resonance points and then quickly rise to about  $e^2/h$  at the resonance points. And most importantly, an anti-resonance point is always accompanied by a resonance point which is very close to it. In the presence of modulation magnetic field, the difference of conductances between these two spins is noticeably large when the inject energy locates in one of the anti-resonance/resonance energy windows. One can tune the Fermi Energy to obtain both large electric and spin current. For example in the energy windows  $[0.11619|t_0|, 0.11789|t_0|]x$ , we obtain the largest spin current density with  $I_\uparrow^{SP} = I_\uparrow - I_\downarrow \approx 5.986nA$  for the spin-up current.

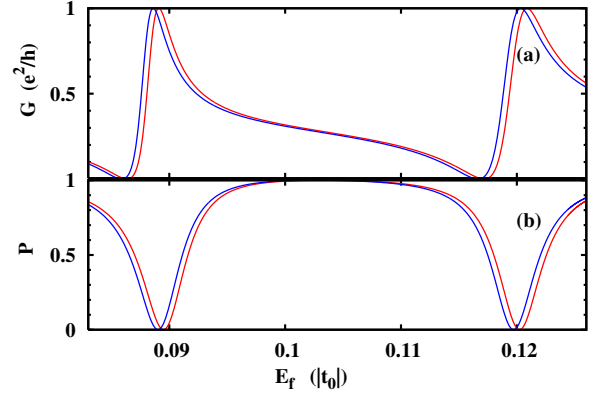


FIG. 2: (Color online) Spin dependent conductances  $G^{\uparrow\uparrow}$  (red curve) and  $G^{\downarrow\downarrow}$  (blue curve) vs the incident energy of the electrons for quasi-one-dimensional (a) and two-dimensional (b).

Like the original QMT, we can also use the a remote gate voltage to control the length of the sidearm. In Fig. 3(b) we present the conductances for different sidearm lengths  $L_s$  but constant  $L_s - L_m$ . In this way we simulate the electronically controlling of the device without changing the magnetic modulation profile, *i.e.* the strength and the positions of the applied magnetic field. One can see from the figure that, the anti-resonance and the corresponding resonance points change with the length of the sidearm as they should have been. For a specified injection energy, when the length of the sidearm changes, not only the conductance but also the SP of output current change. For examples, in the energy window near  $0.0871|t_0|$  one gets about 100% polarized spin-down current when the sidearm is  $60a$  long. Once the length of sidearm is adjusted to  $75a$ , one gets about 8% polarized current but the direction of spin change to up. If one further adjust the length to  $90a$ , the output current is almost non-polarized. It is seen that with this filter one can control the strength, direction and polarization rate of spin current electronically.

In order to further check the robustness of the spin filter we propose, we now add Anderson disorder to the



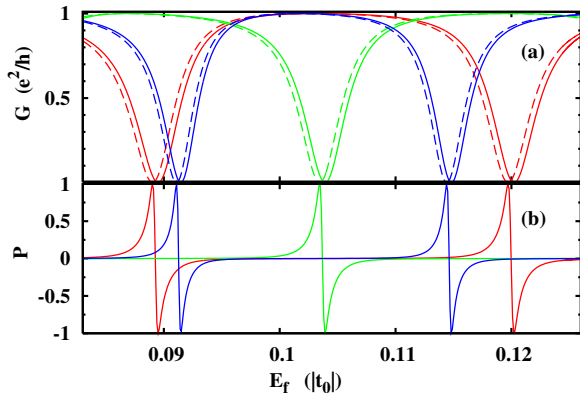


FIG. 3: (Color online) Spin dependent conductances  $G$  (upper panel) and the corresponding spin polarization as functions of the electron energy for different sidearm length and fixed magnetic modulation profile: Red curves:  $L_s = 60 a$ ,  $L_m = 15 a$ ; Green curves:  $L_s = 75 a$ ,  $L_m = 30 a$ ; Blue curves:  $L_s = 90 a$ ,  $L_m = 45 a$ . The solid/dashed curves are conductances for spin-up/down electrons.

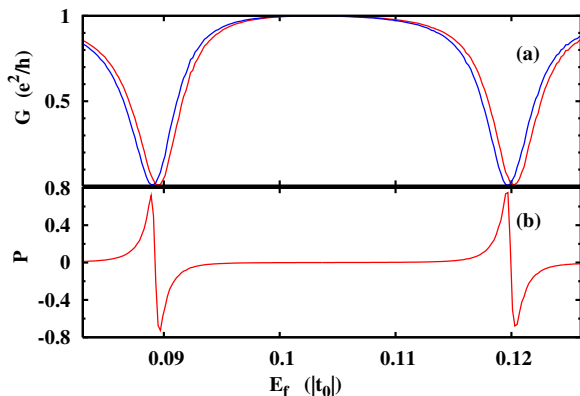


FIG. 4: (Color online) The spin dependent conductance  $G^{\sigma\sigma}$  (a) and SP (b) as functions of Fermi energy for the device with Anderson disorder  $W = 0.005|t_0|$ . The blue and red curves in (a) correspond to  $G^{\downarrow\downarrow}$  and  $G^{\uparrow\uparrow}$  respectively.

system and study its effect on the SP. In Fig. 4, the spin-dependent conductances  $G^{\uparrow\uparrow}$  and  $G^{\downarrow\downarrow}$  as well as the SP are plotted against the energy of the incident electrons with the Anderson disorder included. The strength of the disorder  $W = 0.005|t_0|$ , five times of the modulated potential  $V_0$ . It is found that the disorder decreases the transmission coefficients, but only have slight effect on SP. In some energy windows, one can obtain SP as high as 80%. Therefore the scheme we propose is robust against the disorder.

In summary, we propose a spin filter scheme which enables the electrically and magnetically remote control the spin polarization of output current. The spin filter is a T-stub waveguide with a modulation magnetic field at the tip of the sidearm. In this device, electron conductance drops to the minimum when Fermi energy locates at the anti-resonance points and rises to the maximum at resonance points. With the modulation field, the (anti-)resonance points of spin-up and -down electrons shift apart. Since a pair of the anti-resonance and resonance points are very close to each other, one is able to use moderate magnetic field to produce both large electric and spin currents. Moreover one is able to control the direction and polarization of the output spin current of the T-stub waveguide via a remote gate which tunes the length of the sidearm and therefore realize the remote electronically control of spin current. We further shown that the device is robust against the disorder.

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